

Applied Fields and Waves

Practical Power Amplifier

Group No. 1

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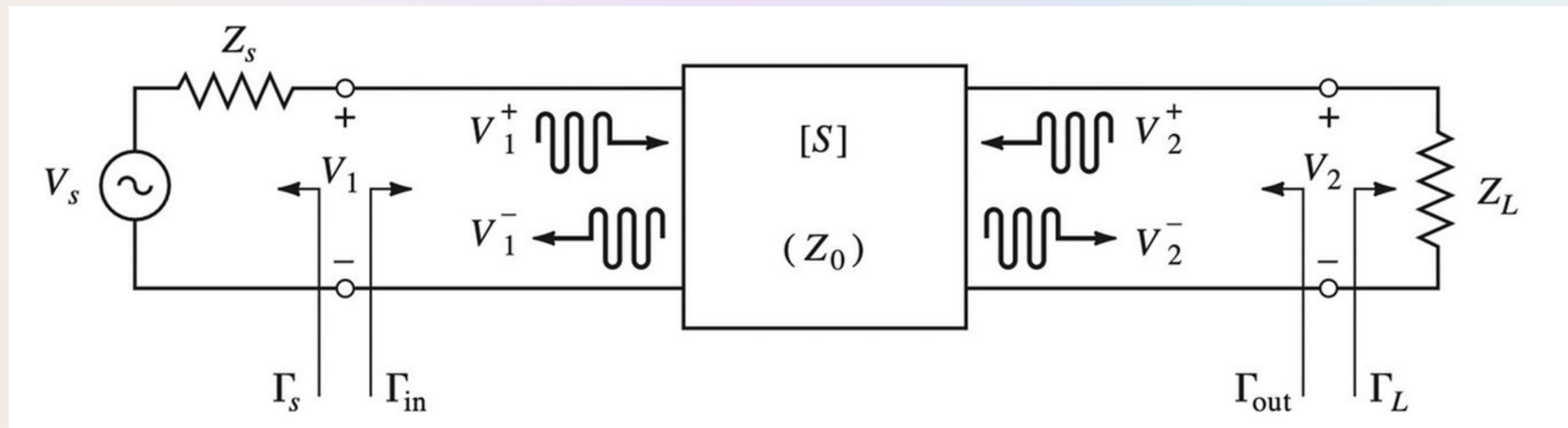
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Nirmit Malik

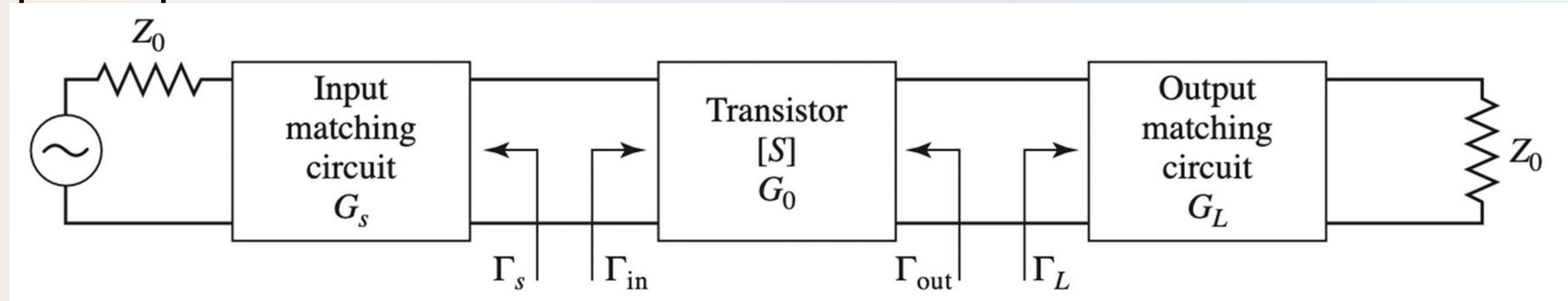
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Introduction

- Power amplifier: Converts low-power signal to a higher power.
- It is a two port network device.
- Used in a wide variety of applications including Wireless Communication, TV transmissions, Radar, and RF heating



- A single-stage transistor amplifier: A circuit where matching networks are used on both sides of the transistor to transform the input and output impedance.



The general transistor amplifier circuit

Drain efficiency
(or collector efficiency)

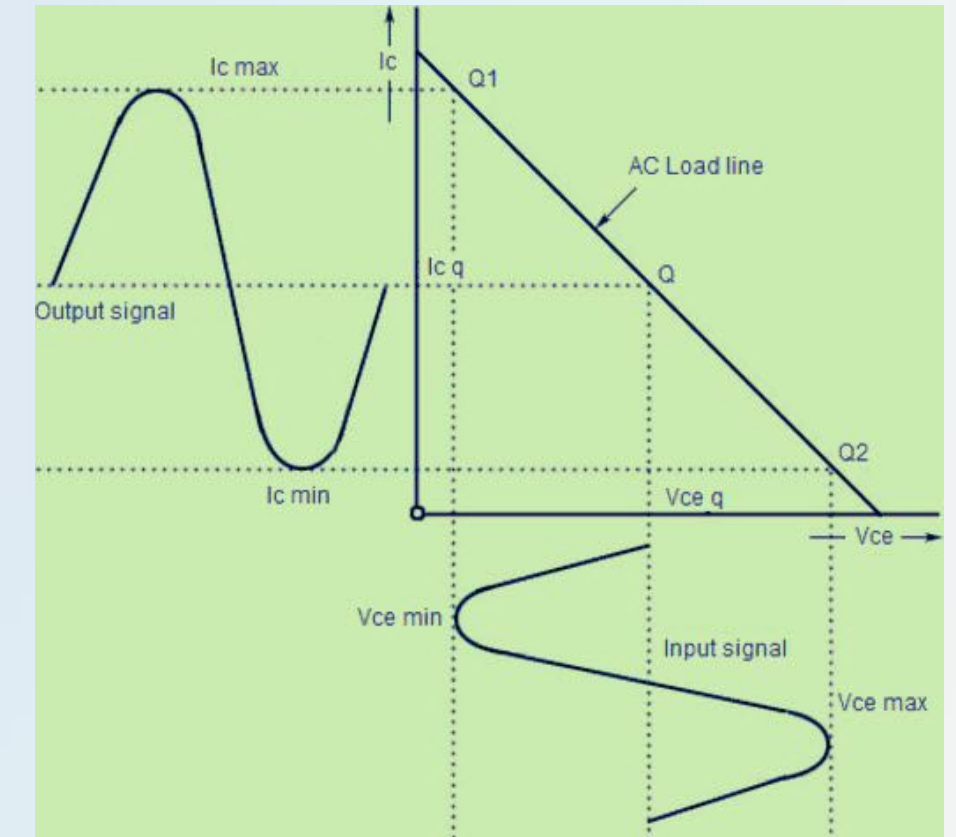
$$\eta = \frac{P_{out}}{P_{DC}}$$

Power added efficiency

$$\eta_{PAE} = PAE = \frac{P_{out} - P_{in}}{P_{DC}}$$

Class A Power Amplifier

- Simplest and most linear amplifier.
- Conduction angle 360 degree.
- Maximum efficiency of this is 50%.
- No distortion of the input signal



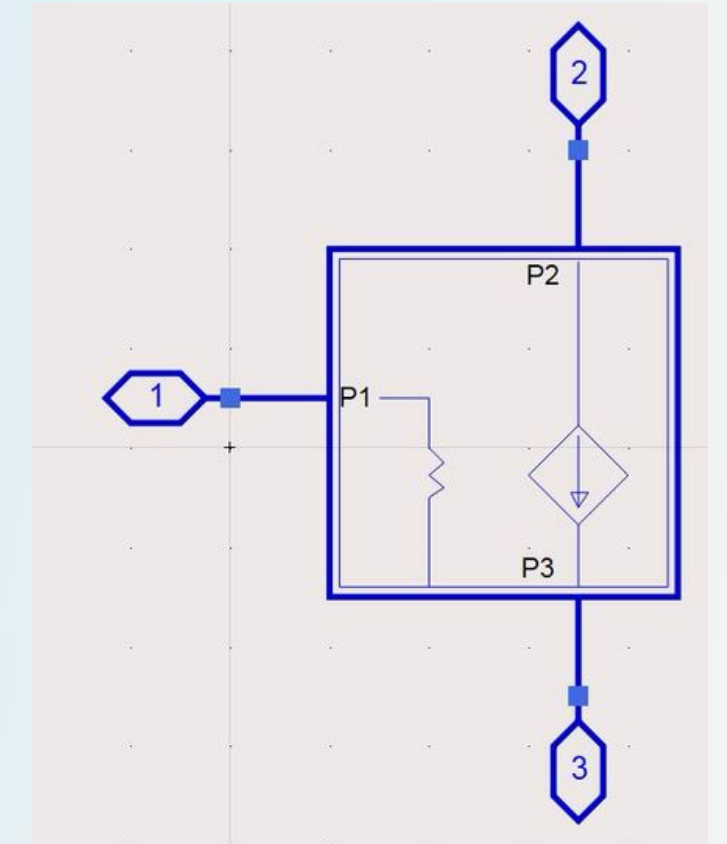
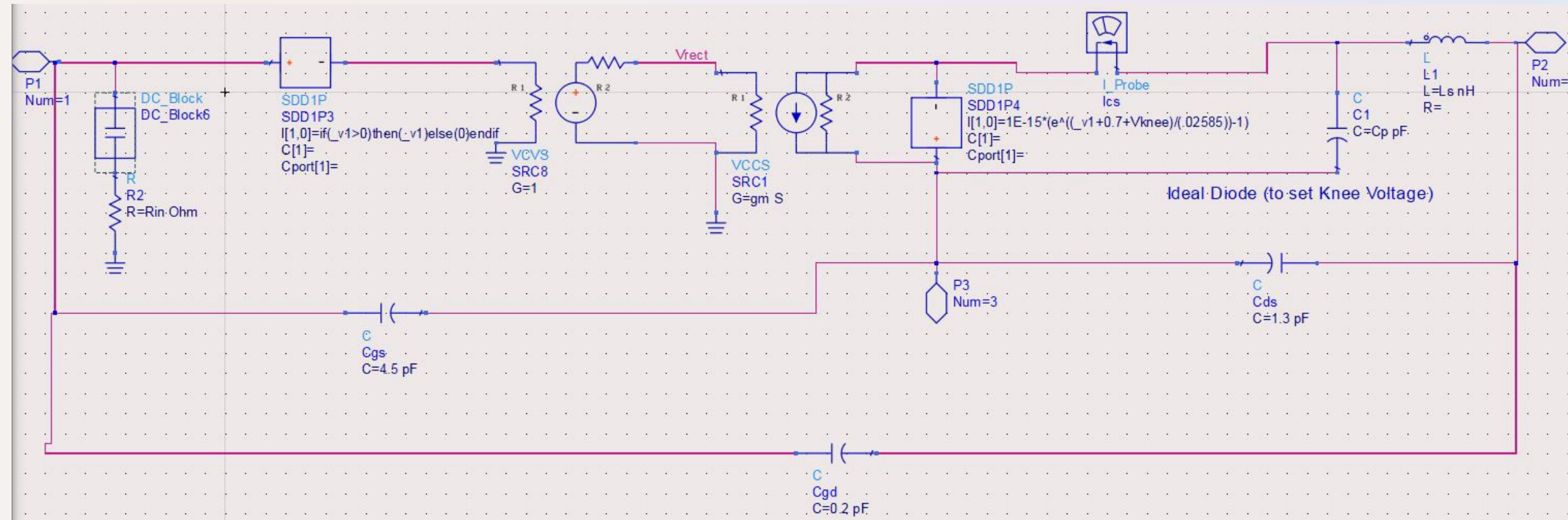
Disadvantages

- Due to the large power supply and heat sink, class A amplifier is costly and bulky.
- It has Poor Efficiency.

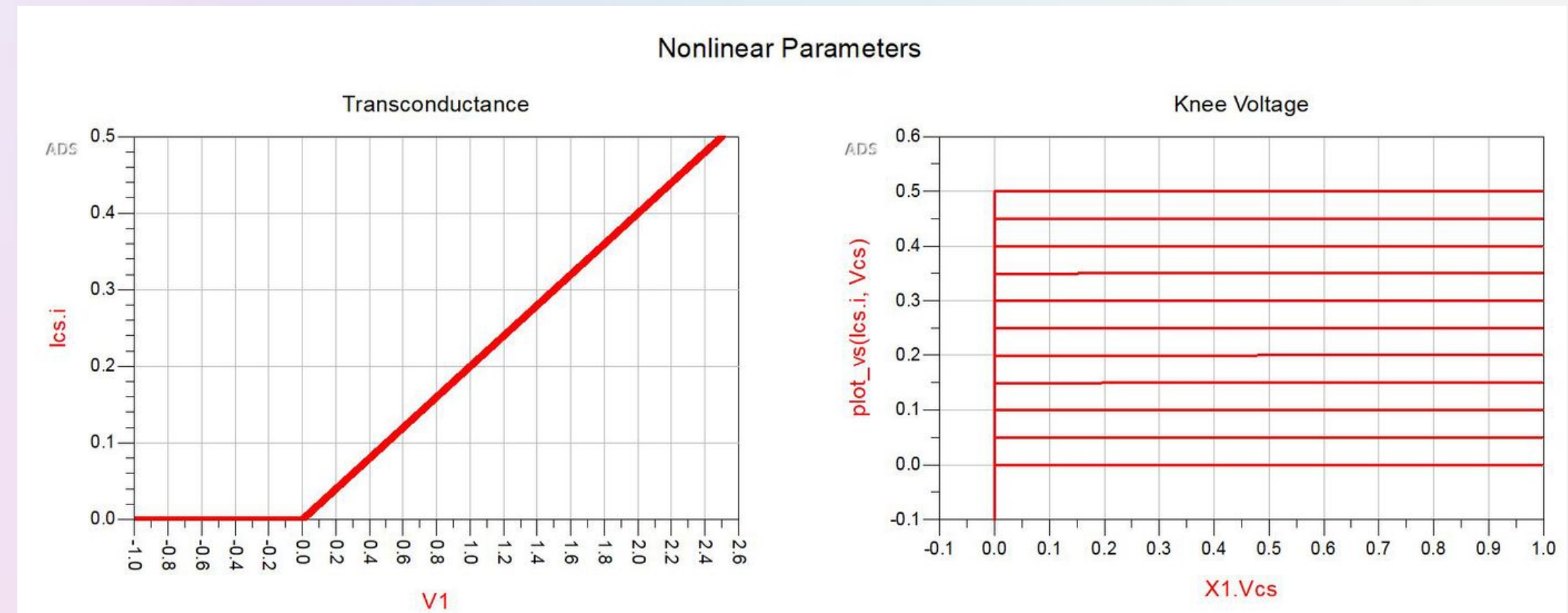
Application

- Places where information in signal is more important than its strength.
- Microphones Pre Amplifiers

Ideal Device

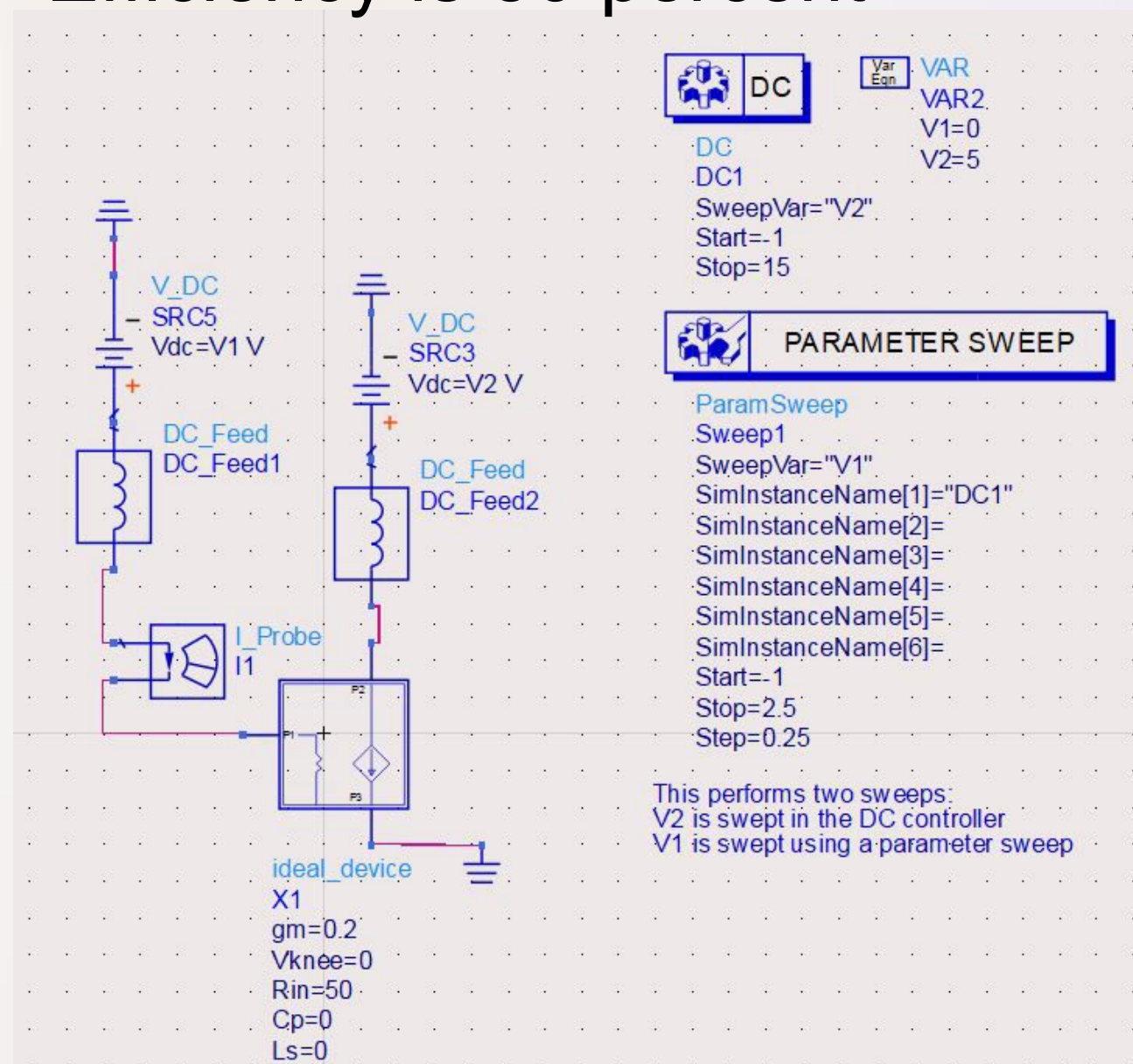


- Made an equivalent circuit for a non linear device
- Use equation for Transconductance and Knee Voltage



DC-Biasing

- Setting a transistors DC operating voltage or current conditions
- Here we set DC bias such that the conduction angle is 360 degree i.e of a Class A amplifier.
- Efficiency is 50 percent

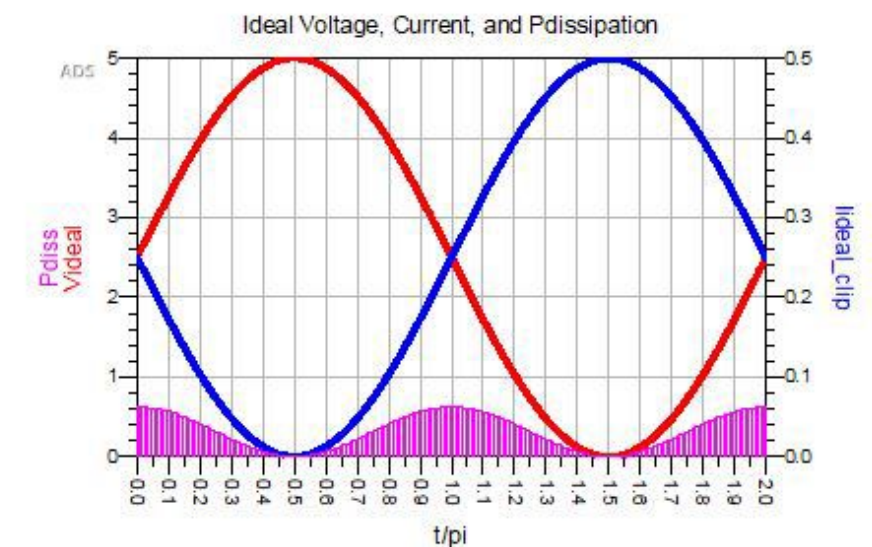
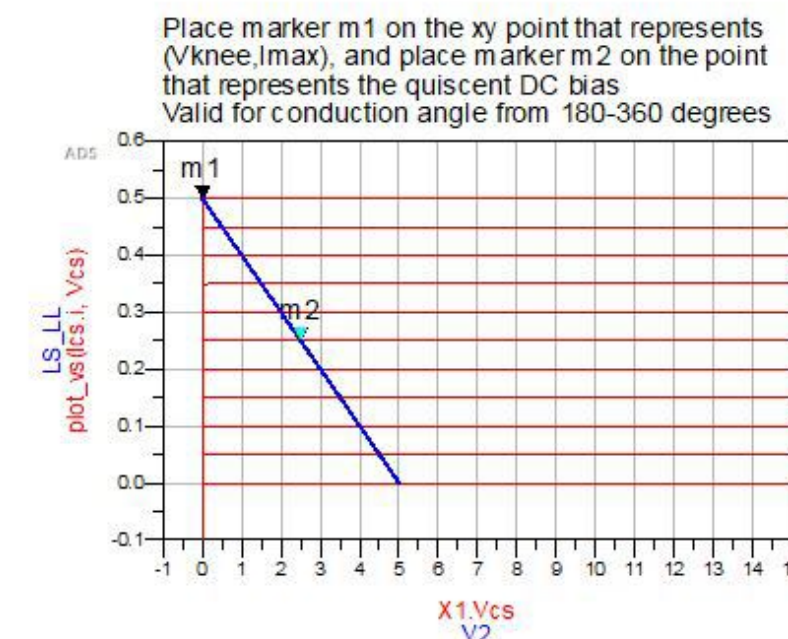


IV Curves from Device, All other calculations based on loadline design equations

m1
X1.Vcs=0.000
plot_vs(lcs.i, Vcs)=0.499
V1=2.500

m2
X1.Vcs=2.500
plot_vs(lcs.i, Vcs)=0.250
V1=1.250

RL
10.024

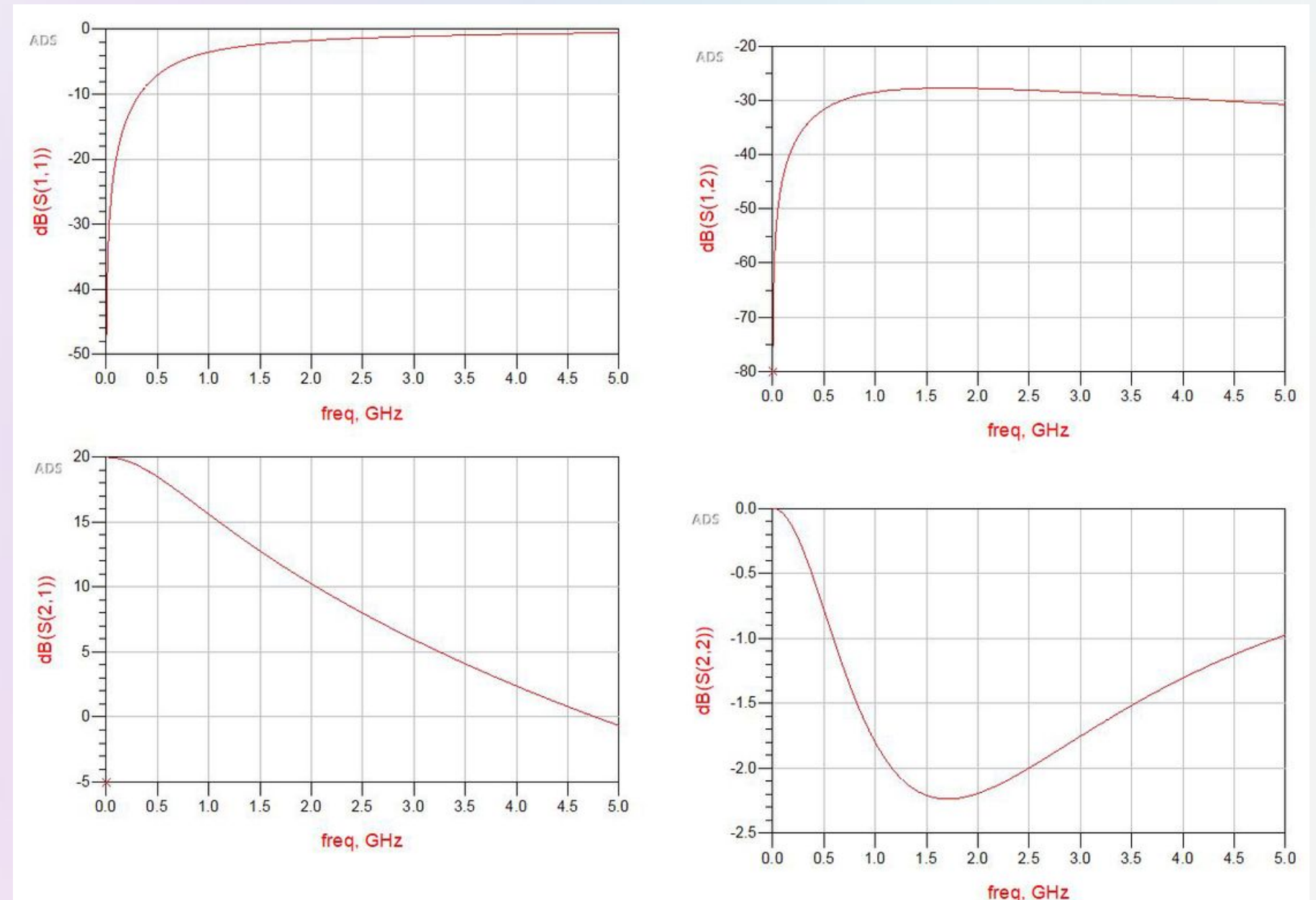
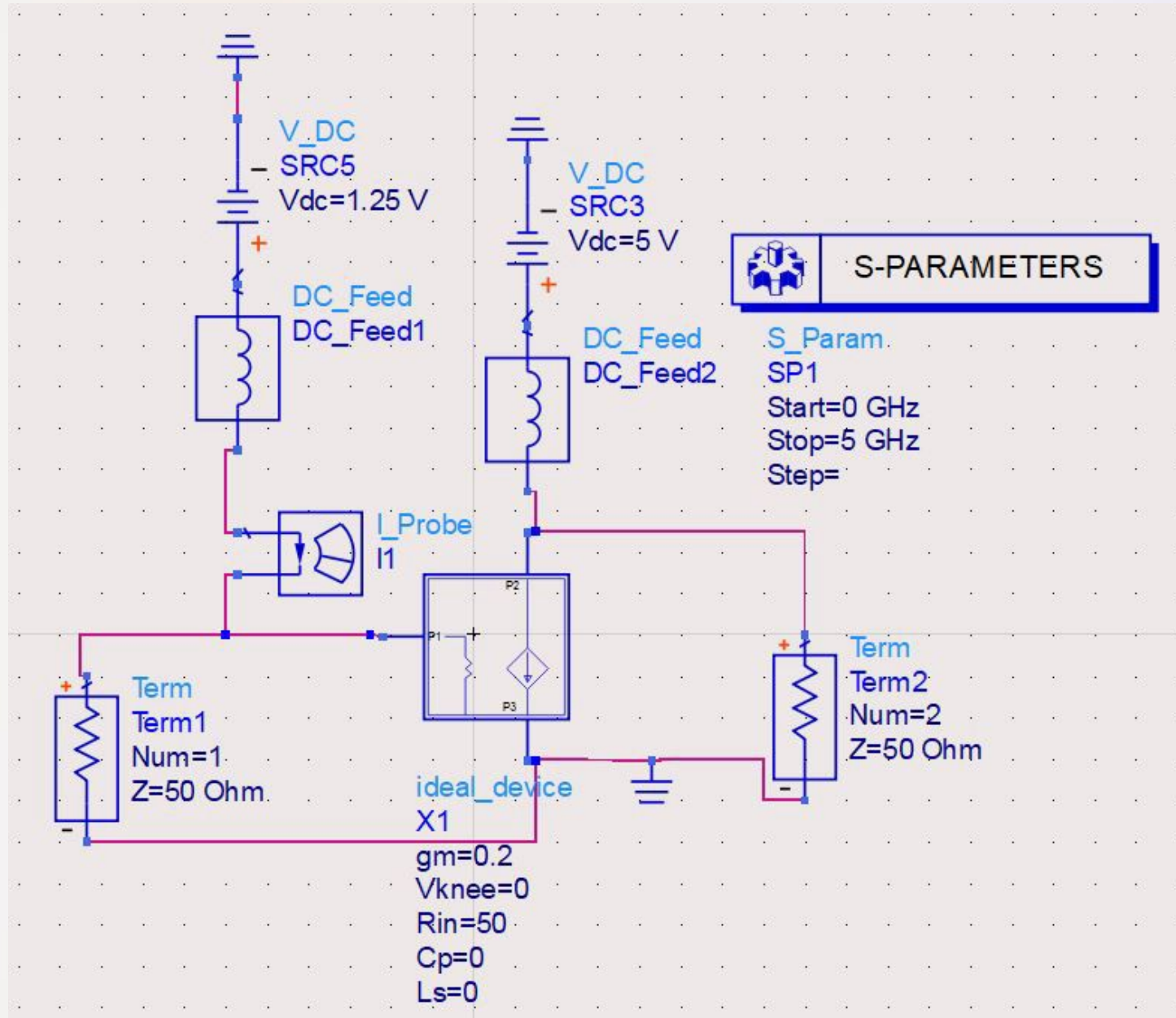


Pout_Max	SS_Gain	LS_Gain	n_max	Idc	Conduction_Angle	Duty_Cycle
24.94	13.02	13.02	49.94	0.25	360.00	100.00

Eqn Zin=50

S-Parameter of DC Bias Ideal Device

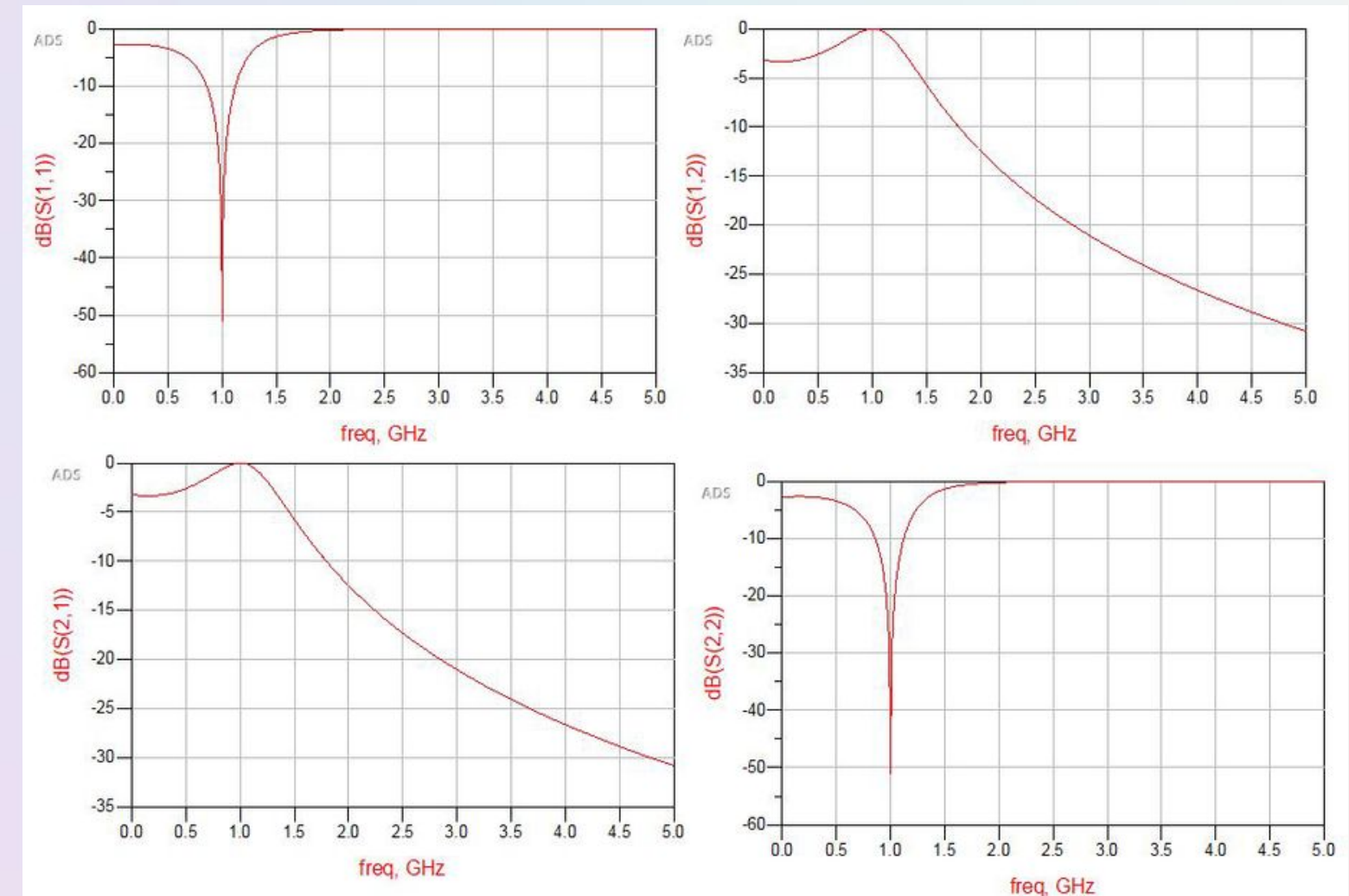
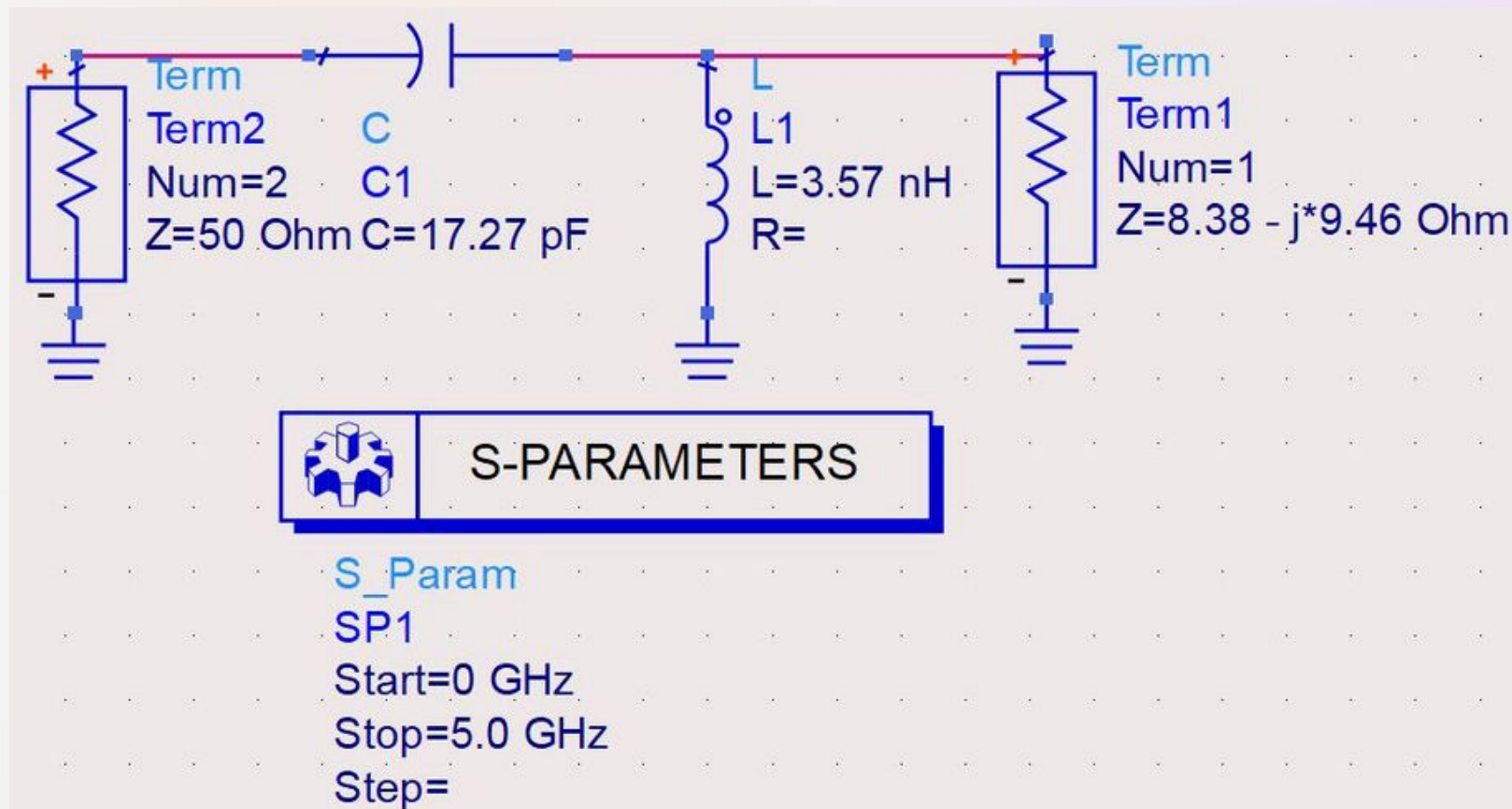
- Use S - parameter tool to sweep over frequency
- It is an ideal device having Dynamic Characteristics of CGH40010



Input matching

- The available power from the source is entirely delivered to the input of the gain element.
- $Z_s = 8.38 + j9.46$ (at 1 GHz)
- $Z_o = 50$ ohm

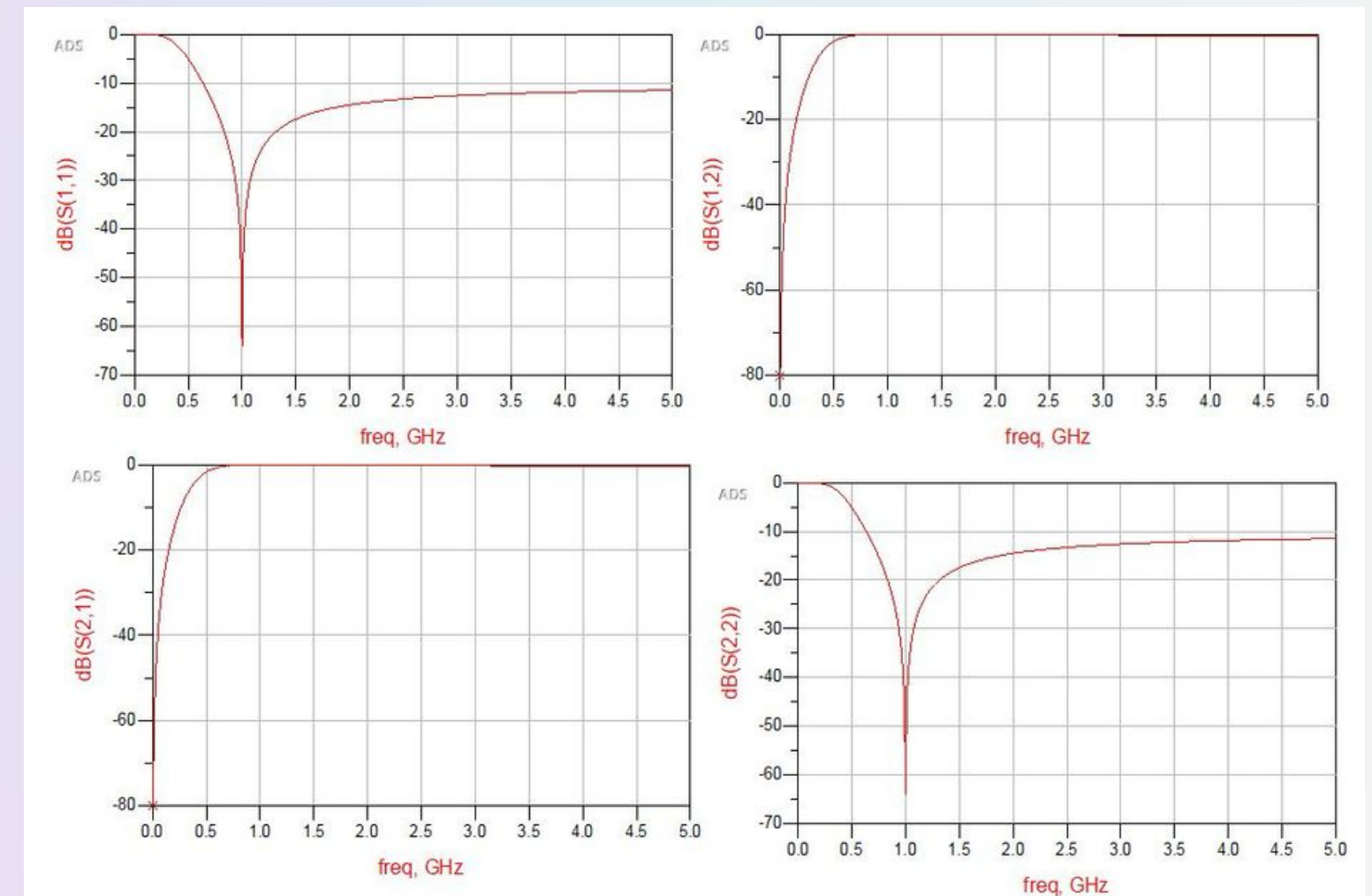
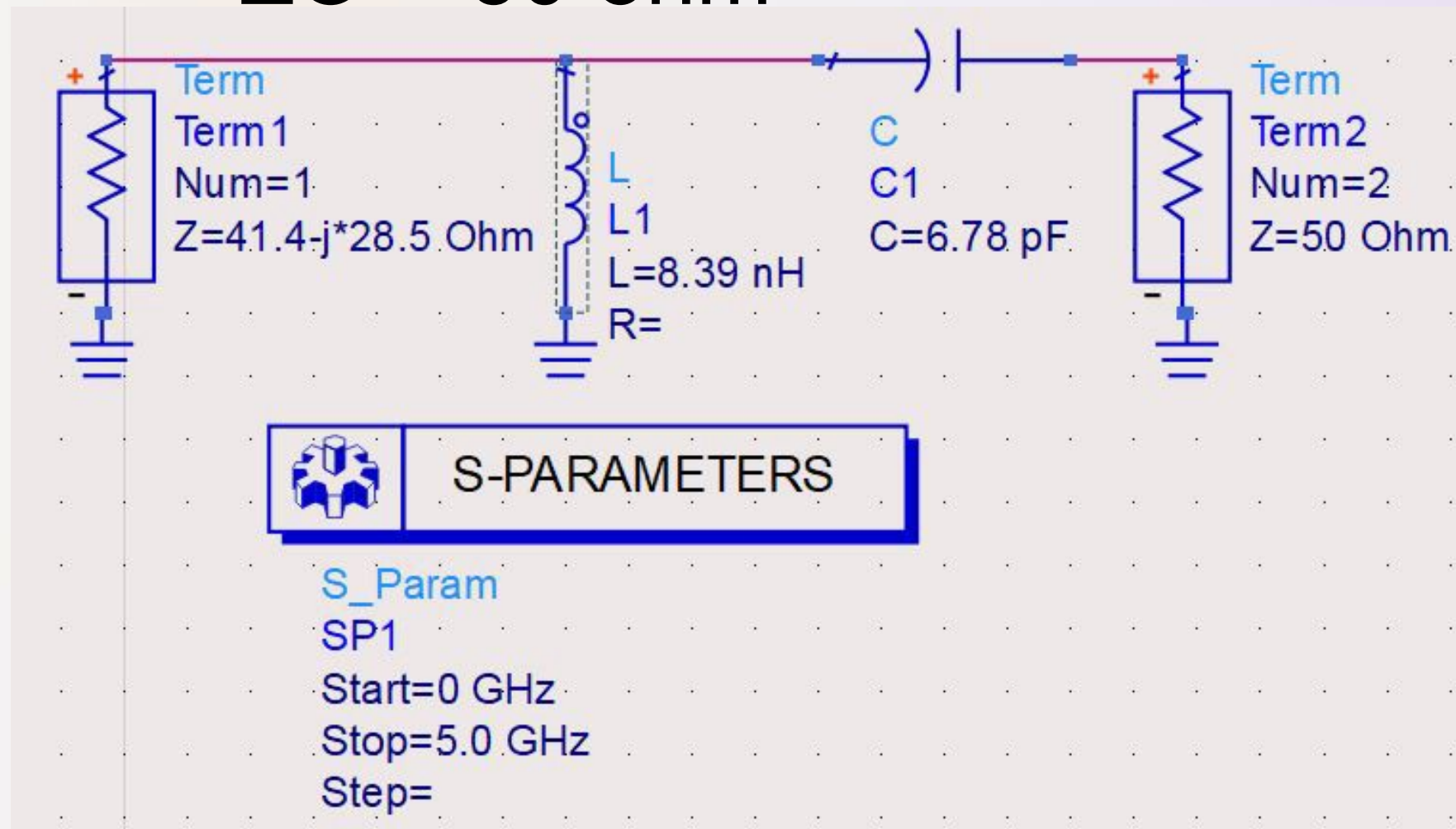
S - parameters



Output matching

- The available power from the output of the gain element is entirely delivered to the load
- $Z_L = 41.4 + j28.5$ ohm (at 1 GHz)
- $Z_O = 50$ ohm

S - parameters



Gain Parameters

- Efficiency is a measure of its ability to convert the DC power (P_{dc}) of the supply, into the signal power delivered to the load (P_{out})
- Power gain: ratio of power dissipated in the load Z_L to the power delivered to the input of the two-port network.
- S_{12} of Transistor is too small. Assume it zero, this make amplifier unilateral.

$$G_S = \frac{1 - |\Gamma_S|^2}{|1 - S_{11}\Gamma_S|^2},$$

$$G_0 = |S_{21}|^2,$$

$$G_L = \frac{1 - |\Gamma_L|^2}{|1 - S_{22}\Gamma_L|^2}.$$

$$G_T = G_S G_0 G_L$$

G_S = Input Matching network Gain

G_0 = Transistor Gain

G_L = Output Matching network Gain

G_T = Unilateral transducer gain

Work Distribution

- Ankit Kumar Pal: Realisation of circuit equivalent of the transistor, DC analysis of the Transistor, and Finding Operating Point
- Sangam Rai: S-parameter calculation of the Model, Input, and Output impedance matching network.
- We together work for presentation and coordinate where is the needed.

References

- Debidas Kundu Sir
- [Keysight Reference](#)
- [Anurag Bhargava Lecture](#)
- [Matching Network](#)
- Microwave Engineering D.M Pozar
- Class Lectures